

## Lessons learned probing power management devices in multi-DUT test format

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## What we will NOT be covering...

- Multi-DUT economics as applied to cost of ownership models etc.
- •RF modelling / performance / characterisation.
- •Sales pitch . This is a TECHNICAL paper, intended to illustrate potential problems and corrective actions as controlled by the laws of physics.



## Main topics in this presentation:

- Overview of Pyramid Probe® technology
- Power management device overview
- Our first quad site power management probe card
- Results from a cantilever card
- Analysis of the problem
- Simulation of probe card and DUT
- Quad site probe card: Take 2.
- Results from the test floor
- What did we learn from this?
- Conclusion & acknowledgements

## Pyramid Probe® Cards



## Mechanical Core Assembly





## Main parts of a cell phone



## Extremely simplified cell phone power management device overview



#### Real DUT has >100 bond pads!

# Our first quad DUT power management probecard.....





## And then you get a phone call.....

- The new probe card is delivered to site.
- There is a substantial backlog of wafers waiting.
- A single site needle card is available, which is working.
- There is high pressure to have the quad site card running.
- This project has the attention of senior management.
- Your new probe card does not appear to work.
- One DUT is fine, the other 3 are failing.
- We need this fixed NOW!
- What time is your flight?



## Single site Cantilever measurement

#### **Start value (I=0) = 5.0v**



#### What does this tell us about the DUT?

- Pass & Fail limits are set by the end user, so the customer is not at liberty to change them.
- Best case is 5.0V, when the current flowing is zero.
- Device seems to have 2 modes, presumably when the regulator is working (Zo=20 ohms) and when the regulator is not working (Zo=80 ohms)
- This is a very marginal test. Even with cantilever at 4.73V, there is only 230mV headroom.

## Measurements from quad site card.



Pass level for SIMVCC (5V mode) test is between 4.5V and 5.5V Cantilever measures 4.73V



4.55V PASS!
4.32V FAIL!
4.38V FAIL!
4.46V FAIL!

But only by 50mV

Notice also variation in results of 230mV from die to die

## Let's take a step back

Version	Site 0	Site 1	Site 2	Site 3	Var.
rev A	4.55V	4.32V	4.38V	4.46V	230mV

- Why is only one DUT passing (barely) and the others failing?
- Why do we see such a large spread in the measurements?

## What are the ideal test conditions?



## What's REALLY happening?



#### Suspicion is these are too high

# We need to make an estimation of Rprobe

#### Rprobe is comprised of 5 series elements:

 A) R<sub>pogo</sub>. This is the resistance between the pogo pin and the PCB.



We know it is low, typically 0.1 ohm.

## Continuing to make an estimation of Rprobe

- B) Rpcb. This is the resistance of the trace on the PCB. Using R=rho x L / A, where:
- Rho=59.6E6 ohm meter (for copper)
- L is typically 5cm, but can vary from 3cm to 9cm depending on where it is and how many layers it uses.
- A is the cross sectional conducting area, an 8 mil wide, 1.4 mil thick copper trace



## This gives Rpcb as around 4 ohms

## Continuing to find Rprobe



**Typically around 0.1 ohms** 

## Membrane DC path resistance



Using same formula, Rmemb comes out to: R=(4.5e7 x 30e-3)/(60e-6 x 5e-6) Around 5 ohms. But, note the different path lengths between DUT's.

## Contact tip resistance on Aluminium





VacMode HV Spot VVD HEVV Sig Mag Lowvacuum 15.0 kV 4.5 10.03 mm 64.00 um BSE 4000

#### **12 microns**



#### **15 microns**





From previous data, we know this is around 0.2 ohm

### Put it all together and what do you get?



## = 0.1 + 4.0 + 0.1 + 5.0 + 0.2 ohms = 9.4 ohms

WAY TOO HIGH! We should be targeting 2-3 ohms or less.

## Modelling and simulation of SIMVCC using Rev A probe card

Version	Site 0	Site 1	Site 2	Site 3	Cantilever
rev A	4.55V	4.32V	4.38V	<b>4.46V</b>	4.73V
Loss	180mV	410mV	350mV	270mV	0.00mV

DUT	Rmemb	Rpcb	Rprobe1	Rmemb	Rpcb	Rprobe2	Rtotal	current	Vdrop	measured loss
	ohms	ohms	ohms	ohms	ohms	ohms	ohms	mA	mV	mV
0	5.4	4.2	10	5.1	0.5	5.9	15.9	10mA	159	180
1	6.3	4.9	11.6	6.4	0.5	7.2	18.8	10mA	188	410
2	6.3	8.4	15.1	6.3	0.5	7.1	22.2	10mA	222	350
3	5.9	5.3	11.6	5.4	0.5	6.2	17.8	10mA	178	270

Probe card resistance varies significantly DUT to DUT But this does not explain fully the measured differences Is the 4.73V from cantilever a valid number?

## Is the cantilever measurement valid?



#### Now we know why we have problems

Version	Site 0	Site 1	Site 2	Site 3	Var.
rev A	4.55V	4.32V	4.38V	4.46V	230mV

- Why is only one DUT passing (barely) and the others failing?
- Because the probe card resistance (Rprobe) is too high
- Why do we see such a large spread in the measurements?
- Because the membrane & PCB path lengths vary from DUT to DUT, and the reference value from the cantilever card is not stable.

### So what can we do to fix this?

## Rev A was made with one metal layer



## We can use 2 metal layers, signal & ground.



## Let's connect all GND pins to GND plane on the new membrane.



# Identify & prioritise all critical outputs from the DUT.

4 DC outputs per DUT
identified & widened
from 60um to 500um
use isolated sections of the membrane ground plane as a conducting layer



#### Note: the symmetrical layout, to give equal path lengths for all 4 DUT's

### What else can we do?

Use 2 PCB interface points instead of 1

For each of the sensitive signals to halve the value of R<sub>int</sub>



Redesign the PCB to use dedicated power planes for these signals.

This will reduce Rpcb significantly.

#### Now what do we have for Rprobe?



## = 0.1 +0.5 +0.05 +0.8 +0.2 ohms = 1.7 ohms

## Much better. But does it work?

## Old compared to new



## Our new results from the test floor

#### Target is 4.5V to 5.5V, cantilever = 4.73V, Theoretical=4.92V

Version	Site 0	Site 1	Site 2	Site 3	Var.
rev A	4.55V	4.32V	4.38V	4.46V	230mV
rev B	4.86V	4.84V	4.88V	4.85V	40mV

All 4 die show bin 1, & higher (almost theoretical) SIMVCCsame DUT4.86V4.87V4.87V4.86V10mV

Contact the same die 4 times by jogging the probecard 1 DUT

DUT to DUT variation of probe card now minimal

**Result-Happy customer, and confidence in the laws of physics** 

## So what did we learn?

- Laws of Physics always apply. Everything on the test floor (tester, prober, DUT, probe card etc) obeys them.
- Understand the function of the device. It's key to making a good probe card. Important to have communication between IC designer, test engineer, probe card apps engineer & membrane designer.
- Don't always trust your first set of measurements.
- Identify and prioritise sensitive signal paths where minimum resistance is necessary.
- New design rules implemented in Cascade design centre following this learning experience. These rules are constantly updated as we continue to learn.
- Since this event, >20 multi-DUT power management designs have been built and used successfully by customers around the world.

## Conclusion (and personal tribute)



"Ye can'nae change the laws of physics!"

But at least you can try to understand and apply them to keep your customer happy and build a better product.

**James Doohan 1920-2005** 

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